## Status of BNL Front End ASIC Design

V. Polychronakos (On behalf of the Development team)

# Outline

#### Motivation/Requirements

□ Example of existing IC – Model for the New Development

Some results – Proof of principle

□ Effort to integrate both current and future IC tests to the SRS

□ Status of the new IC development (Gianluigi de Geronimo)

- Some general information on the BNL IC development process
- Cost/Schedule for prototypes and production quantities
- Status and schedule of the new chip

Some desirable features for muon upgrade detectors

Data Driven System

Real Time Peak Amplitude and Time Detection

- Automatic, on-detector zero suppression
- Dramatic reduction of data bandwidth
- Neighbor channel enabling circuitry (allows relatively high thresholds without losing small amplitudes)
- On-chip ADC (10-12 bits?)
- □ Simultaneous read/write with built-in Derandomizing Buffers
- □ 64 or 128 Channels/chip to match detector element size
- Able to provide Trigger Primitives for possible on-detector track segment finding logic
- Appropriate for a variety of detectors (mMegas, TGC, TPC, GEM, etc) requiring amplitude and time measurement
- Detailed Specifications to be finalized soon

# Example of a BNL TPC ASIC

- Has some key features, peak detector with time stamp but otherwise not suitable for LHC
- □ Useful to demonstrate the principle
- **Technology:** CMOS  $0.25\mu m 2.5 V$ 
  - MiM capacitor and silicide block resistor options
- Power 43 mW

## Front-End Channels 32

- charge preamplifier
- 2<sup>nd</sup> order shaping amplifier
- peak detector
- timing detector
- Integrated calibration capacitor 250 fF ( $\sigma$ =0.1%)
- Shaping time 600 ns
- Channel gain 15mV/fC to 32mV/fC

10/9/2010

## ASIC IC85 Time and Amplitude Measuring Chain

When an event occurs above threshold the discriminator fires and the peak and timing detectors are enabled

At the same time the peak and timing detectors of the two neighbor channels are enabled

The events in the three channels are processed for peak amplitude and peak timing

The two corresponding voltages are stored for each channel



### On-chip zero suppression

#### Amplitude Time



10/9/2010

## "MicroTPC" Operation of mMegas Detector



#### 10/9/2010

## Timing Resolution

Shown for Tdelay = 150 ns



10/9/2010

## Event Display



## **Double Track Events**



10/9/2010

## Precision in determining angle and position



60

50

40

30

V. Polychronakos, 6th RD51 Collaboration Maating

662

0

0

0.005814

0.001714

0.04

560

rad

80.14/46

0.5

# **C-Card Goal**

- This project is to design and build a C-card to facilitate testing of BNL ASICs for micromegas detectors
  - The first C-card will be used to digitize data from the BNL MMC1 card ("hybrid card") that contains two TPCV3 ASICs
    - In the intermediate term, the C-card will be used to digitize data from the next generation (analog) BNL ASIC
    - In the longer term, the C-card will evolve into a front end card containing the final BNL (analog plus digital) ASIC for micromegas

# **C-Card Specification**

## Ken Johns, Joel Steinberg, Dan Tompkins (U. Arizona)

- Will control and acquire data from the MMC1 card (BNL)
- Will transfer digitized and formatted data to the FEC card (Valencia) and SRS (Scalable Readout System) (CERN)
  - This will be the default test beam DAQ system for micropattern detectors at CERN for the next several years
- Will also operate in a standalone mode for debugging and limited DAQ in the lab without FEC card and SRS system

## **C-Card Progress**

#### □ Schematic in progress

10/9/2010





# Gianluigi de Geronimo

Front-end IC for Charge-interpolating
Position-sensitive Detectors
Could work for both TGC and Micromegas
Detectors

Instrumentation Division V. Polychronakos, 6th RD51 Collaboration Meeting BNL

. . .

10/9/2010

#### Typical front-end electronics channel



#### **Subcircuits**

- Low-noise, low-power charge amplifiers
  - gas, liquid, solid state detectors
  - capacitances from 10<sup>-14</sup> to 10<sup>-8</sup> F
- Switched and continuous adaptive reset
- High-order filters, stabilizers, drivers peak time / gain adjustment
- Single- and multi-level discriminators
- Peak and time detectors, derandomizers
- Analog memories and multiplexers
- Counters and digital memories
- Configuration registers
- ESD protections
- Calibration pulse generators
- Analog-to-digital converters
- Digital-to-analog converters
- Precision band-gap references
- Temperature sensors
- Readout control logic
- Low-voltage differential signaling
- Current-mode analog and digital interface/chronakos, on RD5 Collaboration Meeting increase by the years



ASIC for 3D CZT **Position Sensitive Detectors** 

- 128 channels
- 2 mW/channel
- 13 x 10 mm<sup>2</sup>
- 300,000 transistors
- CMOS 250 nm

#### ASIC Design Flow



From concept to ready-for-production:

1 - 2 cycles, 2 - 3 years, 3-6 FTE (depending on complexity)

Higher functionality and complexity means more resources and expertise , 10/9/29/2010 risk, longer development time, 6th RD51 Collaboration Meeting

#### ASIC Fabrication : Prototyping

Major foundries accept designs from multiple customers (MPW)

20 mm reticle

BNL ASIC is here (20 mm<sup>2</sup>, ~ 60,000 transistors)



#### ASIC Fabrication : Production

#### Major foundries accept purchase of dedicated run



#### VMM1 ASIC: Architecture



- 64 channels
- adj. polarity, adj. maximum charge (0.11 to 2 pC), adj. peaktime (25-200ns)
- derandomizing peak detection (10-bit) and time detection (1.5ns)
- integrated threshold with trimming, sub-threshold neighbor acquisition
- integrated pulse generator and calibration circuit
- analog monitor, channel mask, temperature sensor
- continuous measurement and readout, derandomizing FIFO
- 10/9/2010 few mW per channel, chip-to-chip (freighbop) com unication, unication for the stinger face



#### VMM1 ASIC: Schedule and Status

	schedule	status/notes
Analog section	Jul-Oct 2010	in progress
Peak/time detection	Nov-Dec 2010	scheduled
Digital section	Jan-Feb 2010	scheduled
Physical layout	Mar-May 2010	scheduled
Fabrication 1 <sup>st</sup> prototype	Jun-Sep 2010	CMOS 130nm, 1.2V, MPW

